

Docket No.: M4065.0151/P151-B
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Vishnu K. Agarwal, et al.

Application No.: 09/930,958

Group Art Unit: 2814

Filed: August 17, 2001

Examiner: Theresa T. Doan

For: MULTILAYER ELECTRODE FOR A
FERROELECTRIC CAPACITOR

#12D Audt
M. Brunson
7/11/03

SUPPLEMENTAL AMENDMENT

MAIL STOP: AF
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

This paper is in response to the Advisory Action of June 6, 2003, maintaining the rejection of claims 55, 57, 58, 60 and 125, please amend the application as follows:

IN THE CLAIMS:

Please rewrite claim 55 as follows:

55. (twice amended) A memory cell, comprising:

a substrate;

a transistor including a gate on said substrate and a source/drain region in said substrate disposed adjacent to said gate;

a capacitor comprising an electrode having a layer comprising platinum-rhodium material and a non-oxide layer comprising platinum material formed on

1620025 v1; YXFD01LDOC